

FORM PTO-1449 (modified)
To: U.S. Department of Commerce
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Patent and Trademark Office

Atty.
Dkt. No.

M#

Client Ref.

273243

PC0033A Reg

**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

Applicant: JOHNSON et al.

Appln. No.: Not Yet Assigned

Filing Date: February 15, 2002

Date: February 15, 2002

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Examiner: Not Assigned

Group Art Unit: Not Asgnd

U.S. PATENT DOCUMENTS

Examiner's Initials*		Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
<i>Me</i>	AR	4,824,690	04/1989	HEINECKE et al.	313	231.31	
<i>I</i>	BR	4,891,118	01/1990	OOIWA	204	231.31	
<i>Me</i>	CR	4,935,661	06/1990	HEINECKE et al.	313	231.31	
	DR	4,993,358	02/1991	MAHAWILI	118	715	
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	JR						
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	MR						
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FOREIGN PATENT DOCUMENTS

		Document Number	Date MM/YYYY	Country	Inventor Name	English Abstract		Translation Readily Available	
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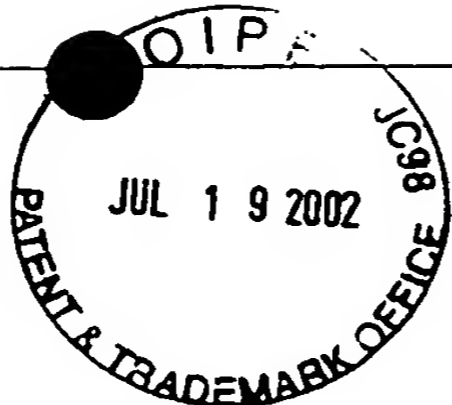
OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

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Applicant: JOHNSON et al.

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Examiner: Not Assigned

Group Art Unit: 1762

U.S. PATENT DOCUMENTS

Examiner's Initials*		Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
<i>ju</i>	AR	5,688,357	11/1997	HANAWA	156	345.28	
	BR	4,993,358	02/1991	MAHAWILI	118	715	
	CR	4,935,661	06/1990	HEINECKE et al.	313	23.31	
	DR	4,891,118	01/1990	OOIWA et al.	204	298.34	
	ER	4,824,690	04/1989	HEINECKE et al.	427	577	
	FR	4,500,563	02/1985	ELLENBERGER et al.	117	710	
	GR	4,413,022	11/1983	SUNTOLA et al.	117	93	
	HR	4,401,507	08/1983	ENGLE	416	65	
	IR	4,263,088	04/1981	GORIN	438	32002	
	JR	4,058,430	11/1977	SUNTOLA et al.	117	93	
	KR	3,979,235	09/1976	BOUCHER	117	93	
	LR	3,721,583	12/1970	BLAKESLEE	117	93	
	MR	3,677,799	11/1970	HOU	427	569	
<i>ju</i>	NR	5,164,040	11/1992	ERES et al.	427	600	

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	QR						

OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

<i>ju</i>	RR	Bird, Molecular Gas Dynamics and the Direct Simulation of Gas Flows, Claredon Press, 1994, pp. 2-3.					
	SR	Gentry et al., "Ten-microsecond pulsed molecular beam source and a fast ionization detector," Rev. Sci. Instru, 49(5), May 1978, pp. 595-600.					
	TR	Samukawa et al., "Pulse-time modulated electron cyclotron resonance plasma etching for highly selective, highly anisotropic, and less-charging polycrystalline silicon patterning," J. Vac. Sci. Technol. B 12(6), Nov/Dec 1994, pp. 3300-3305.					
	UR	Sugai et al., "Diagnostics and control of high-density etching plasmas," Mat. Res. Soc. Symp., Proc. Vol 406, 1996, pp. 15-25.					
	VR	Yeon et al., "Study of particulate formation and its control by a radio frequency power modulation in the reactive ion process of SiO2 with CF4/H2 Plasma" J. Vac. Sci. Technol. A 15(1), Jan/Feb 1997, pp. 66-71.					
<i>ju</i>	WR	Bates, et al., "Fast gas injection system for plasma physics experiments," Rev. Sci. Instrum. 55(6) June 1984, pp. 934-939.					

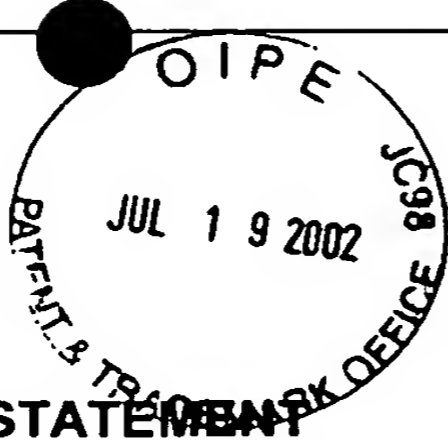
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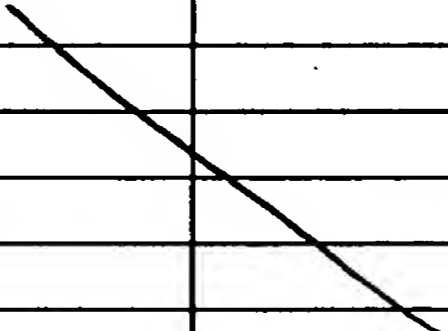
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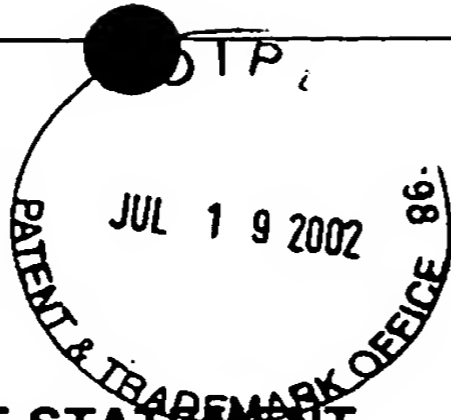
RR	Otis et al., "A simple pulsed valve for use in supersonic nozzle experiments," Rev. Sci. Instr., 51(8) Aug 1980, pp. 1128-1129.				
SR	Cross et al., "High repetition pulsed nozzle beam source," Rev. Sc. Instrum. Vol. 53 No. 1, January 1982, pp. 38-42.				
TR	Kendall, "Pulsed gas injection for on-line calibration of residual gas analyzers," J. Vac. Sci. Technol. A 5(1), Jan/Feb 1987, pp. 143-148.				
UR	Behlen et al., "Dynamics of radiationless processes studied in pulsed supersonic free jets: some naphthalene lifetimes," Chemical Physics Letters, Vol. 60, No. 23, 15 January 1979, pp. 364-367.				
VR	Saenger, "Pulsed molecular beams: a lower limit on pulse duration for fully developed supersonic expansions," J. Chem. Phys. 75(5), 1 Sept. 1981, pp. 2467-2469.				
WR	Bassi et al., "Pulsed molecular beam source," Rev. Sci. Instrum. 52(1), Jan 1981, pp. 8-11.				

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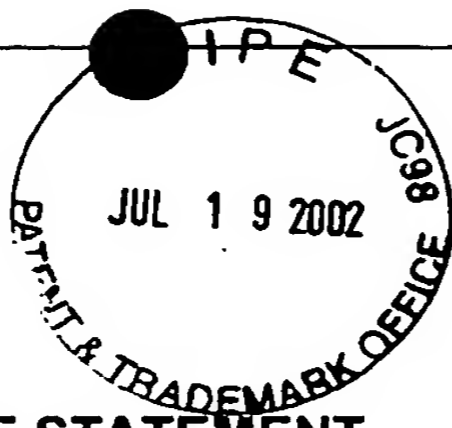
OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

RR	Andressen et al., "Characteristics of a piezoelectric pulsed nozzle beam," Rev. Sci. Instrum. 56(11), November 1985, pp. 2038-2042.				
SR	Balle et al., "A new method for observing the rotational spectra of weak molecular complexes: KrHCl," J. Chem. Phys. 72(2), 15 January 1980, pp. 922-932.				
TR	Gentry et al., "Resolved single-quantum rotational excitation in HD+He collisions: first results from a unique molecular beam apparatus," Journal of Chemical Physics, Vol. 67, No. 11, 1 December 1977, pp. 5389-5391.				
UR	Ohtake et al., "Reduction of topography-dependent charging damage by the pulse-time-modulated plasma," 1998 Dry Process Symposium, V-1, pp. 97-102.				
VR	Matsui et al., "Effect of pulse modulated plasma on a charge build-up of the microscopic structure," 1998 Dry Process Symposium, V-1, pp. 85-90.				
WR	Ono et al., "Selectivity and profile control of poly-Si etching by time modulation bias method," 1998 Dry Process Symposium, V-1, pp. 141-146.				

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OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

RR	Ozeki et al., "Pulsed jet epitaxy of III-V compounds," Journal of Crystal Growth 107 (1991) 102-110 North-Holland, pp. 102-110. ✓				
SR	Ozeki et al., "Growth of GaAs and AlAs thin films by a new atomic layer epitax technique," Thin Solid Films, 174 (1989), pp. 63-70.				
TR	Ozeki et al., "New approach to the atomic layer epitaxy of GaAs using a fast gas stream," Apply. Phys. Lett. 53 (16), 17 October 1988, pp. 1509-1511.				
UR	Samukawa, "Highly selective and highly anisotropic SiO2 etching in pulse-time modulated electron cyclotron resonance plasma," Journal of Appl. Phys. Vol. 33 (1994), Pt. 1, No. 4B, pp. 2133-2138.				
VR	LaBelle et al., "Effect of Precursors on the Properties of Pulsed PECVD Fluorocarbon Thin Films," NSF/SRC Engineering Research Center for Environmentally Benign Semiconductor Manufacturing Thrust - a Teleconference, November 6, 1997, 23 pp.				
WR					

Examiner

Robert McDonald

Date Considered:

7/4/03

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